



Publisher's Note: Growth and Characteristics of *a*-Plane GaN on ZnO Heterostructure [*J. Electrochem. Soc.*, 159, H290 (2012)]

Huei-Min Huang,^a Chin-Chi Kuo,^a Chiao-Yun Chang,^a Yuan-Ting Lin,^a Tien-Chang Lu,^b Li-Wei Tu,^b and Wen-Feng Hsieh^a

^a*Department of Photonics, National Chiao Tung University, Hsinchu 30050, Taiwan*

^b*Department of Physics, National Sun Yat-Sen University, Kaohsiung 80424, Taiwan*

© 2013 The Electrochemical Society. [DOI: [10.1149/2.022303jss](https://doi.org/10.1149/2.022303jss)] All rights reserved. Published January 15, 2013.

This article was published on January 12, 2012, with an incorrect affiliation designation for author Yuan-Ting Lin on page H290. The article was corrected online on November 14, 2012.